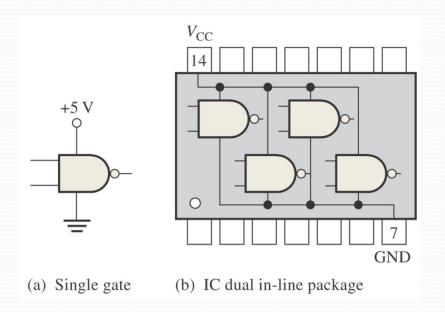
Chapter 12 Integrated Circuit Technologies

OUTLINE

- Basic Operational Characteristics and Parameters
- CMOS Circuits
- TTL Circuits
- Practical Considerations in the Use of TTL
- Comparison of CMOS and TTL Performance

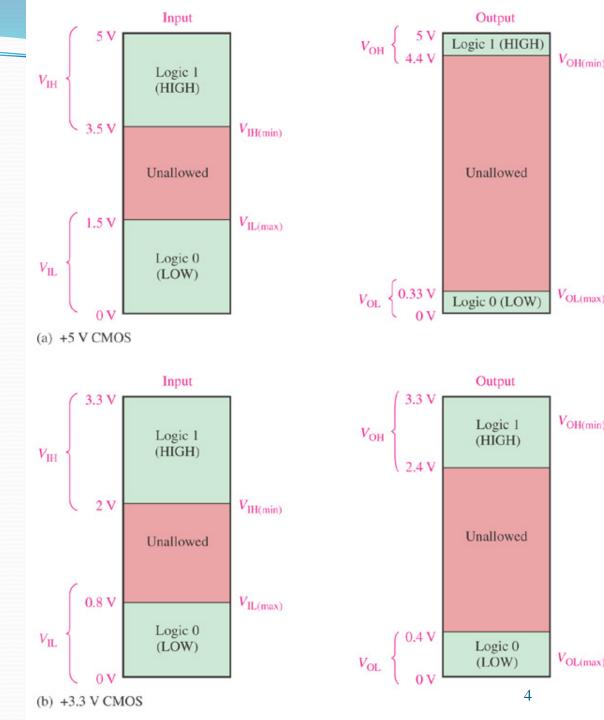
12.1 Basic Operational Characteristics and Parameters

- DC Supply Voltage
 - TTL: +5V
 - CMOS
 - +5V
 - +3.3V
 - +2.5V
 - +1.2V

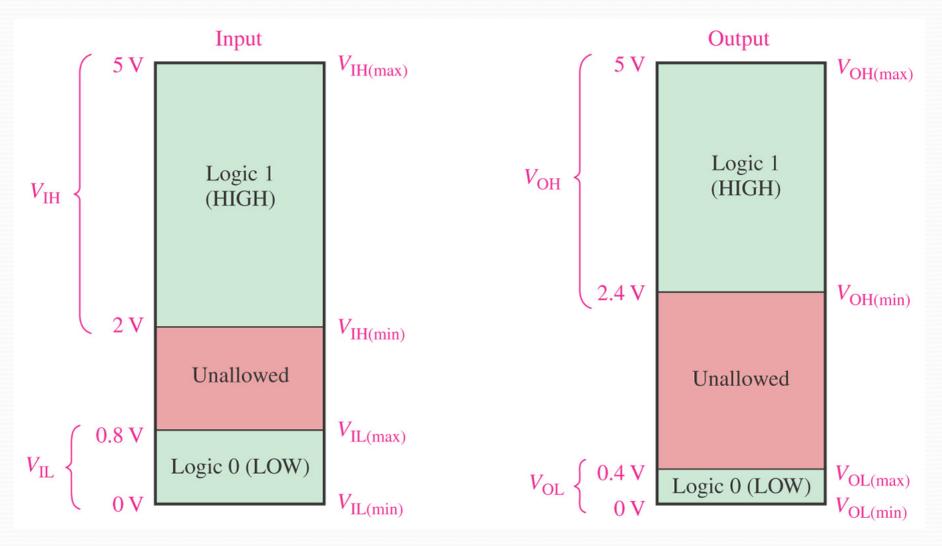


CMOS Logic Levels

- \bullet V_{IL} , V_{IH}
- \bullet V_{OL} , V_{OH}

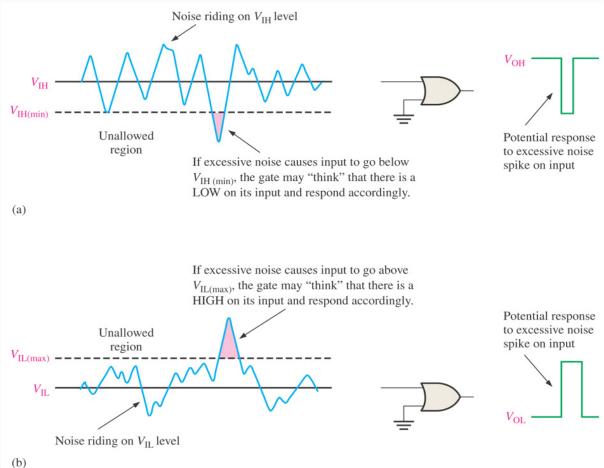


TTL Logic Levels



Noise Immunity

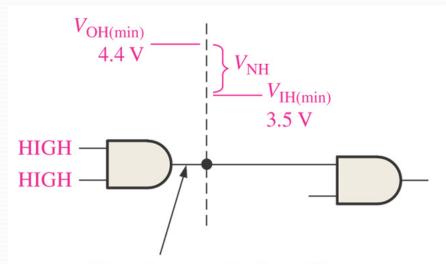
- Noise induced in electrical circuits can present a threat to the proper operation of circuits.
- In order not to be adversely affected by noise, a logic circuit must have a certain amount of noise immunity.



Noise Margin

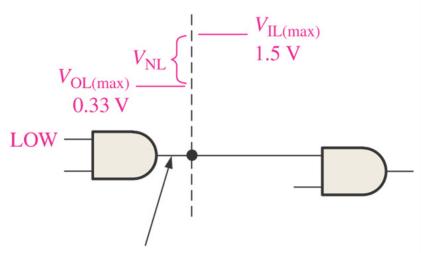
$$V_{\rm NH} = V_{\rm OH(min)} - V_{\rm IH(min)}$$

$$V_{NL} = V_{IL(\max)} - V_{OL(\max)}$$



The voltage on this line will never be less than 4.4 V unless noise or improper operation is introduced.

(a) HIGH-level noise margin



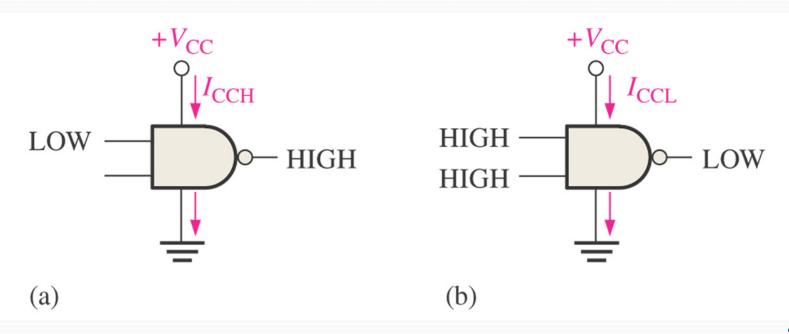
The voltage on this line will never exceed 0.33 V unless noise or improper operation is introduced.

(b) LOW-level noise margin

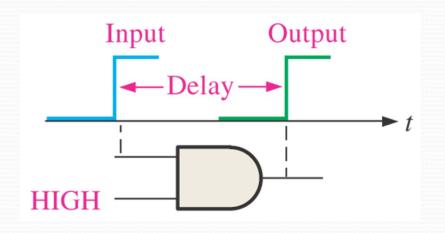
Power Dissipation

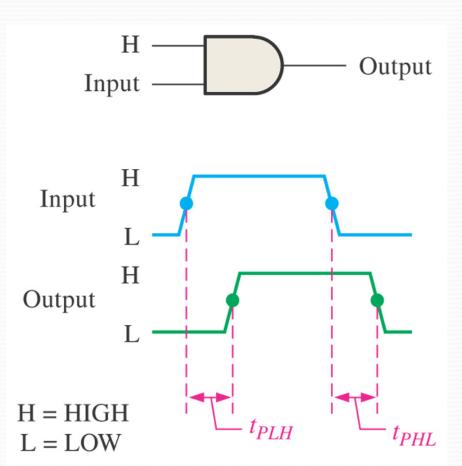
- TTL circuits: power dissipation is constant over its range of operating frequencies.
- CMOS: power dissipation is frequency dependent

$$P_D = V_{CC} I_{CC}$$



Propagation Delay Time





- Speed-Power Product
 - A basis for the comparison of logic circuits when both propagation delay time and power dissipation are important considerations in the selection of the type of logic to be used in a certain application.

Loading and Fan-Out

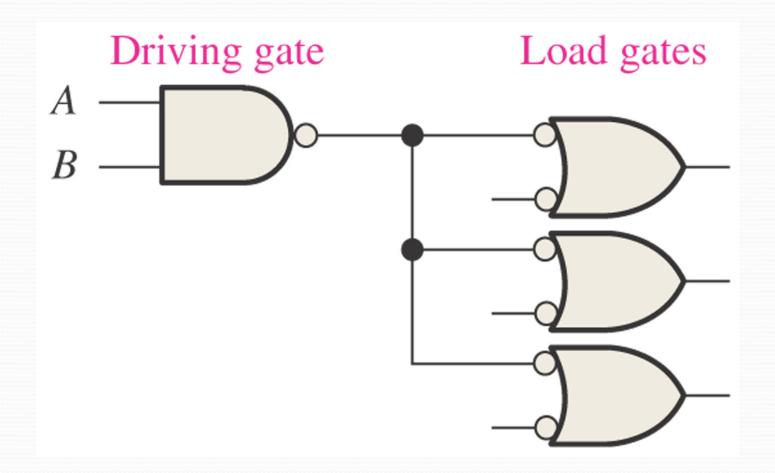


Figure 14–11 Capacitive loading of a CMOS gate.

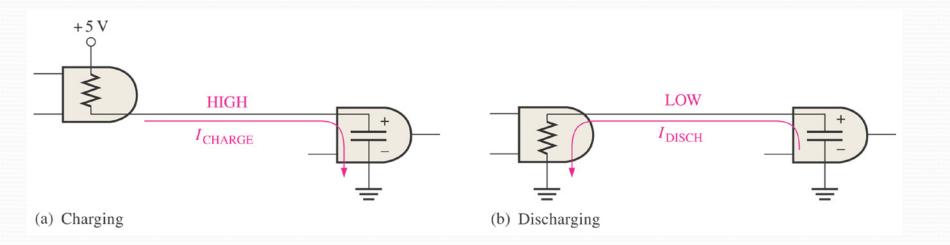


Figure 14–12 Basic illustration of current sourcing and current sinking in logic gates.

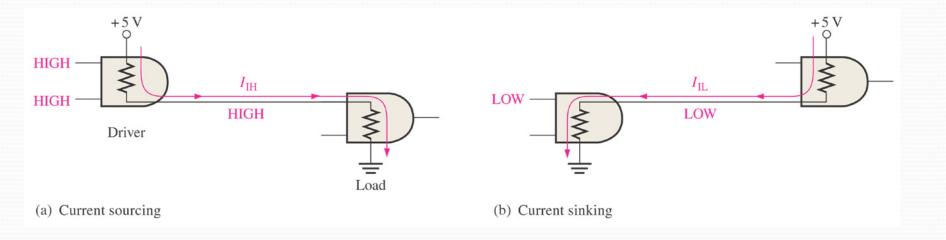


Figure 14–13 HIGH-state TTL loading.

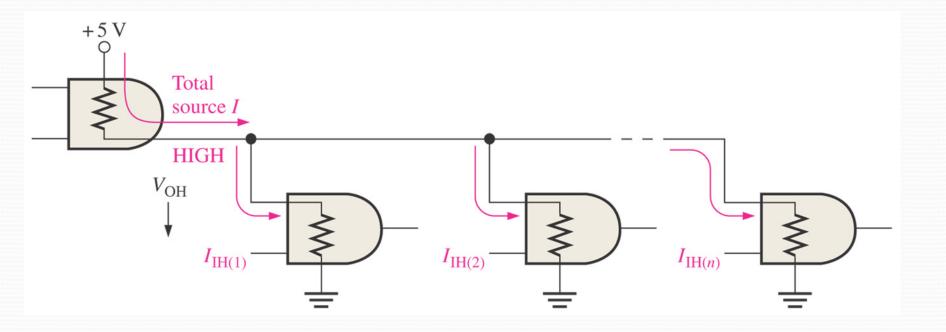
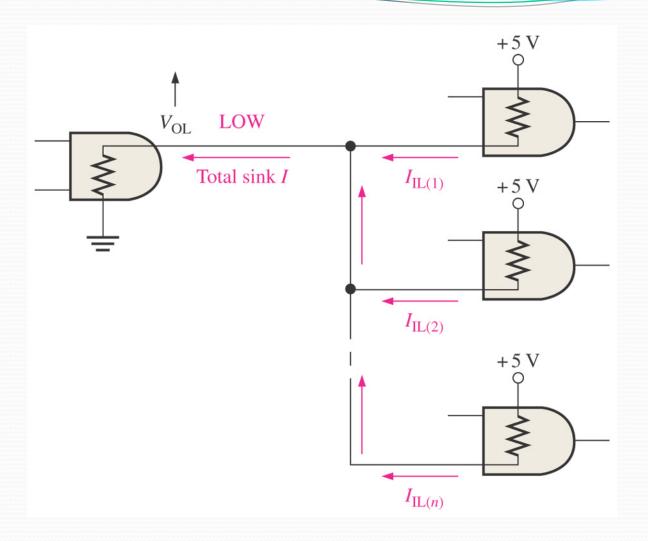


Figure 14–14 LOW-stage TTL loading.

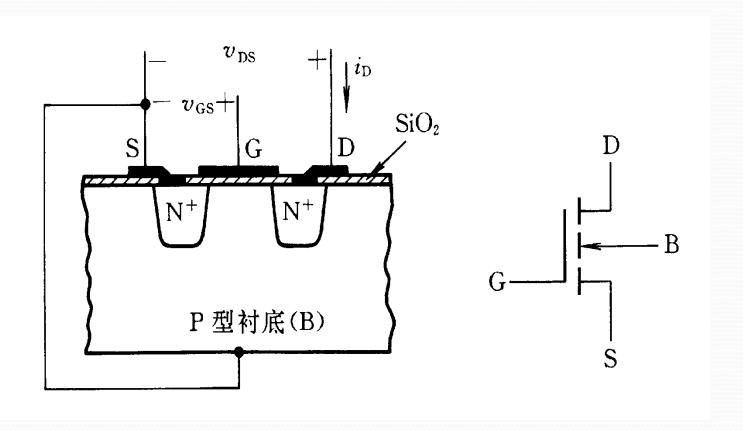


12.2 CMOS Circuits

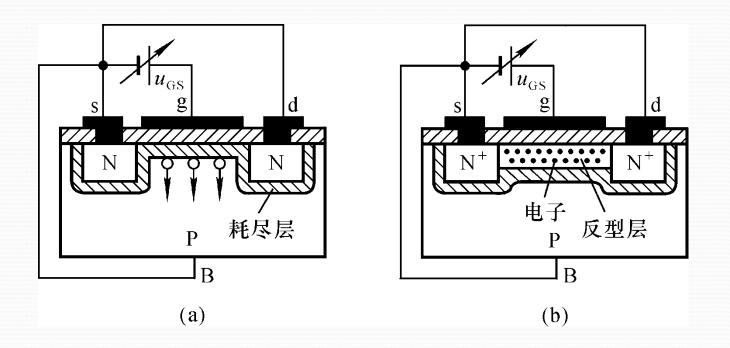
- CMOS: Complementary Metal-Oxide Semiconductor
- Complementary: an n-channel MOSFET and a pchannel MOSFET are used

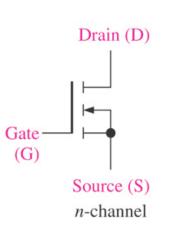
The MOSFET

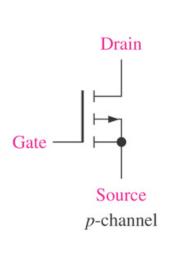
- Two types
 - P-channel
 - N-channel
- Three terminals
 - Gate, drain and source

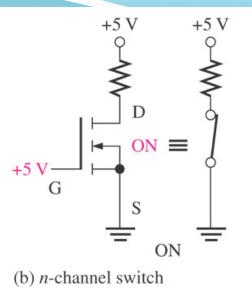


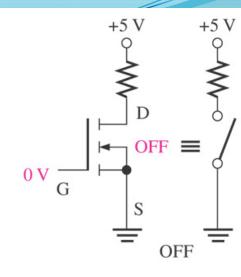
The Structure and Symbol of N-channel MOSFET



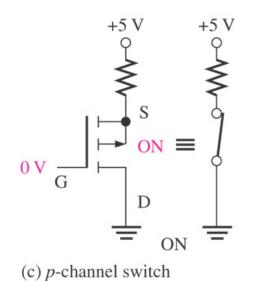








(a) MOSFET symbols



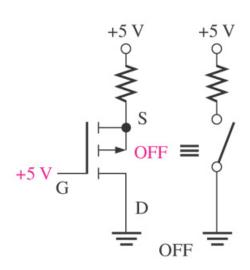
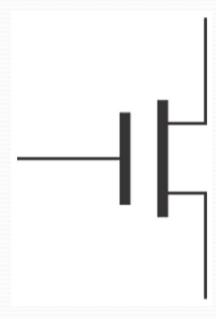
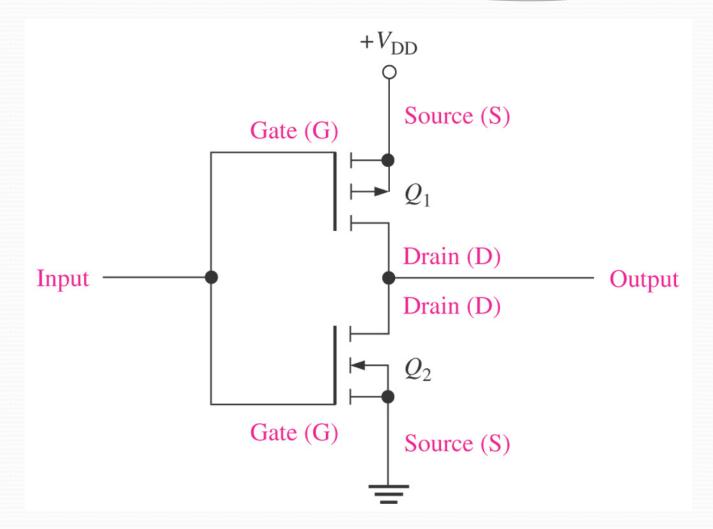


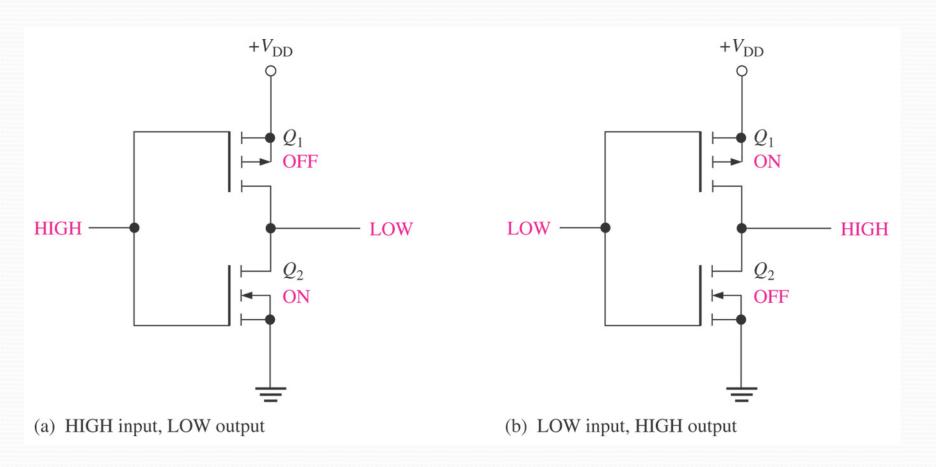
Figure 14–16 Simplified MOSFET symbol.

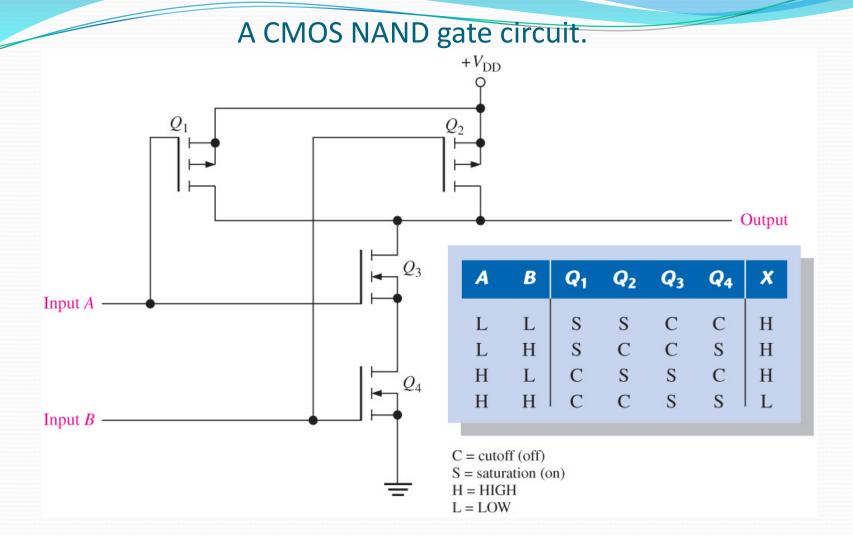


A CMOS inverter circuit.

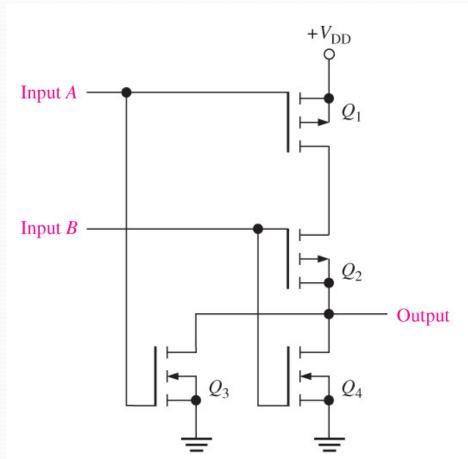


Operation of a CMOS inverter.





A CMOS NOR gate circuit.



		Q_1				
L	L	S S C C	S	C	C	Н
L	Н	S	C	C	S	L
Н	L	C	S	S	C	L
Н	Н	C	C	S	S	L

C = cutoff (off)

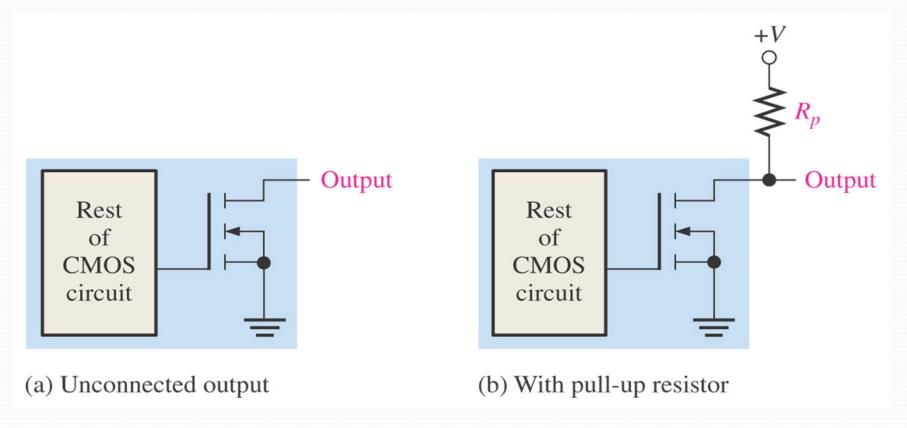
S = saturation (on)

H = HIGH

L = LOW

Open-drain CMOS gates

• The drain terminal of the output transistor is unconnected and must be connected externally to $V_{\rm DD}$ through a load.



The three states of a tristate circuit.

• HIGH, LOW and high-Z

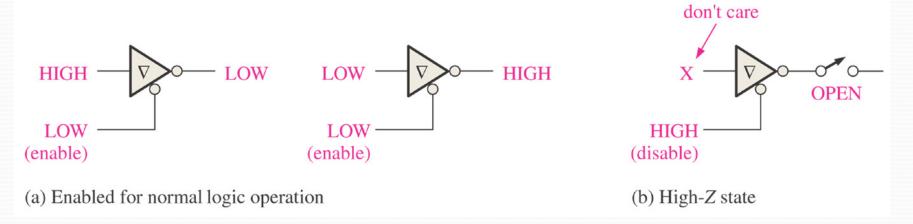
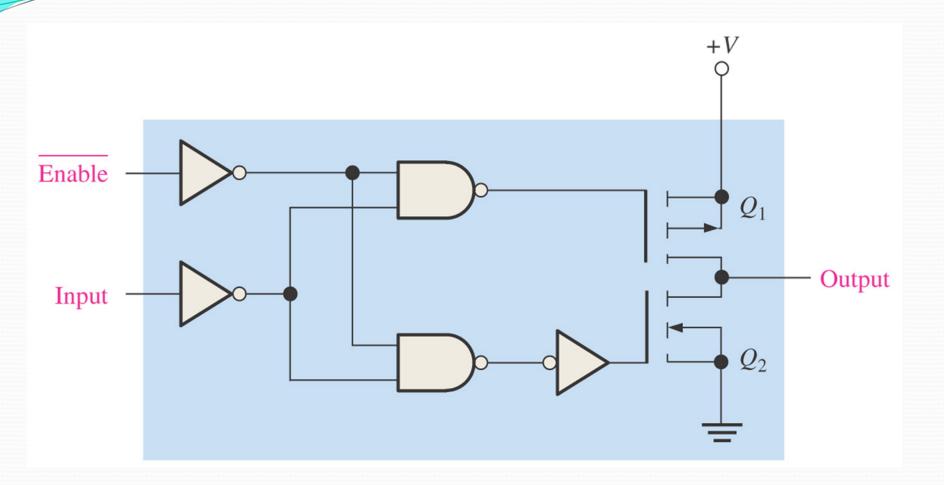


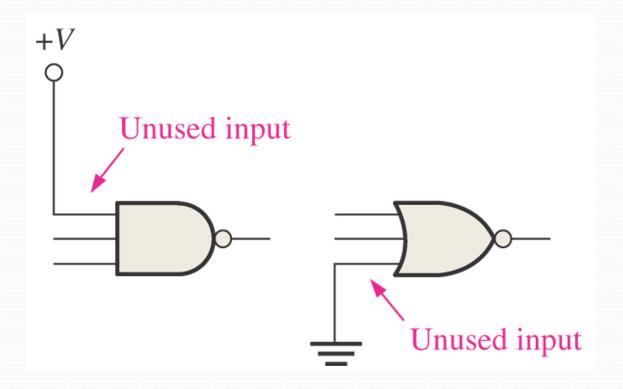
Figure 14–23 A tristate CMOS inverter.



Precautions for handling CMOS

- When CMOS devices are removed from the foam, the pins should not be touched.
- Do not place CMOS devices in polystyrene foam or plastic trays.
- All tool, test equipment, and metal workbenches should be earth-grounded.
- Do not insert CMOS devices into sockets or PC boards with the power on.
- All unused inputs should be connected to the supply voltage or ground.
- After assembly on PC boards, protection should be made.

Figure 14–24 Handling unused CMOS inputs.

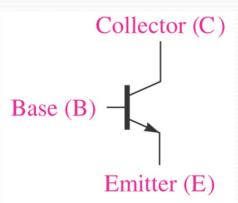


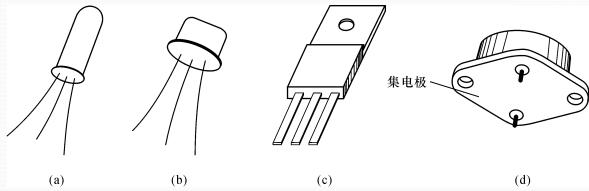
12.3 TTL Circuits

- TTL: Transistor-transistor logic
- With totem-pole output

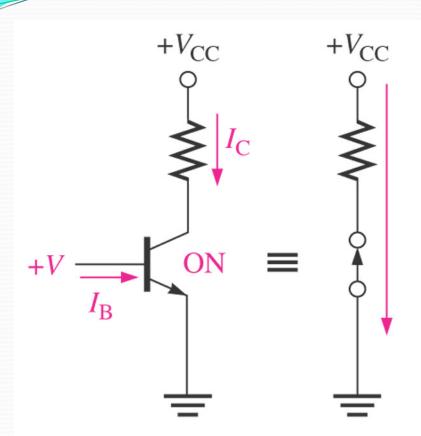
The Bipolar Junction Transistor

- Three terminals
 - Base, emitter, and collector Base (B)

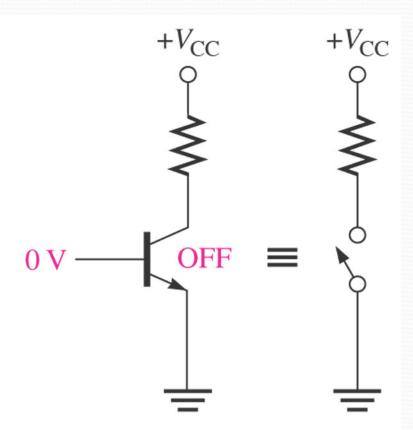




The ideal switching action of the BJT

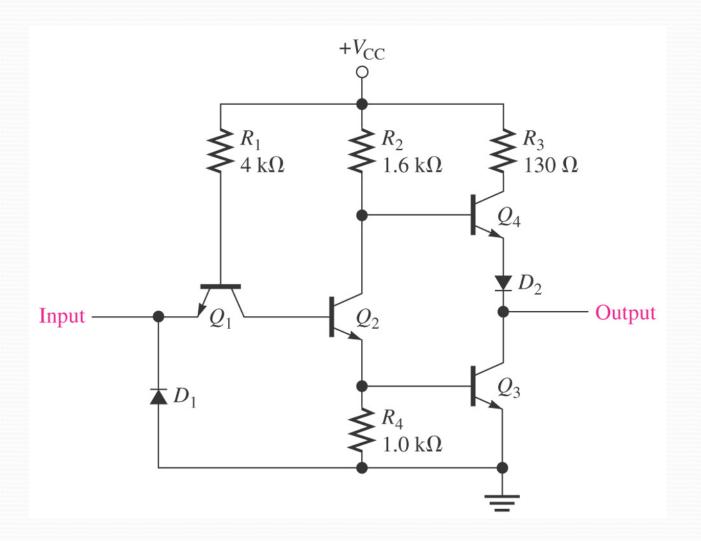


(a) Saturated (ON) transistor and ideal switch equivalent

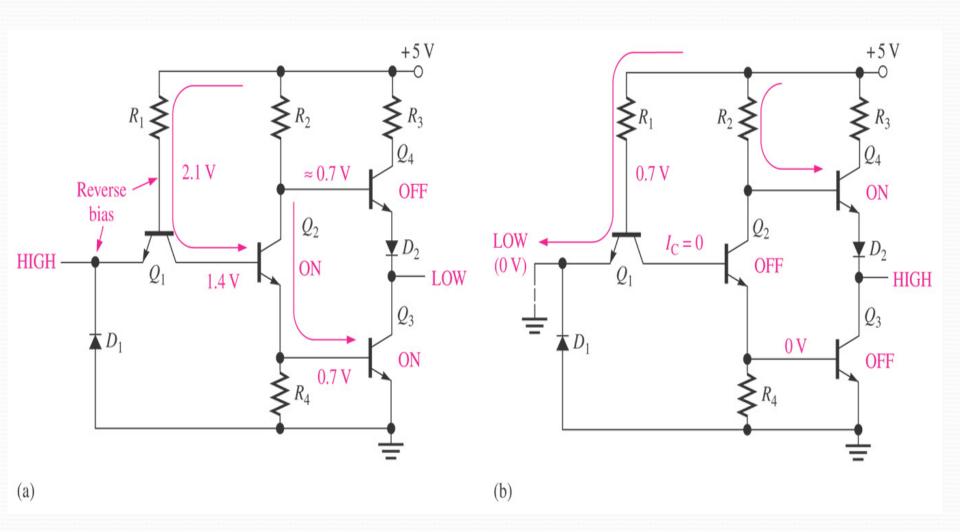


(b) OFF transistor and ideal switch equivalent

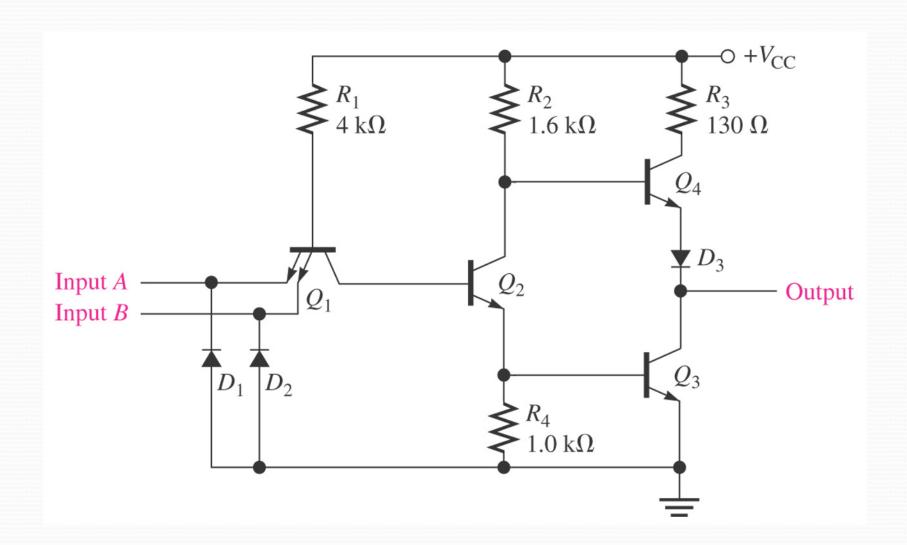
A standard TTL inverter circuit.



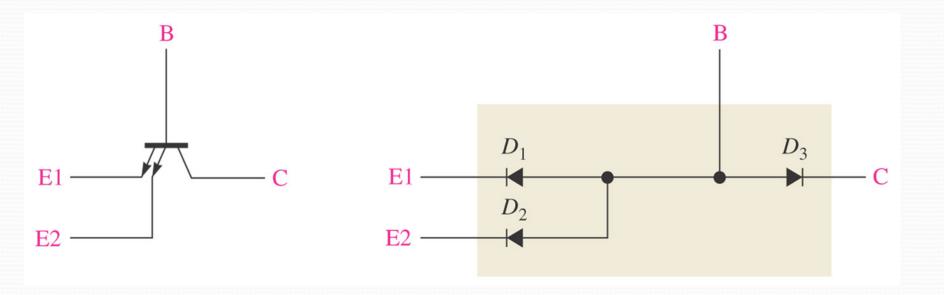
Operation of a TTL inverter



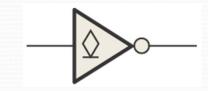
A TTL NAND gate circuit.

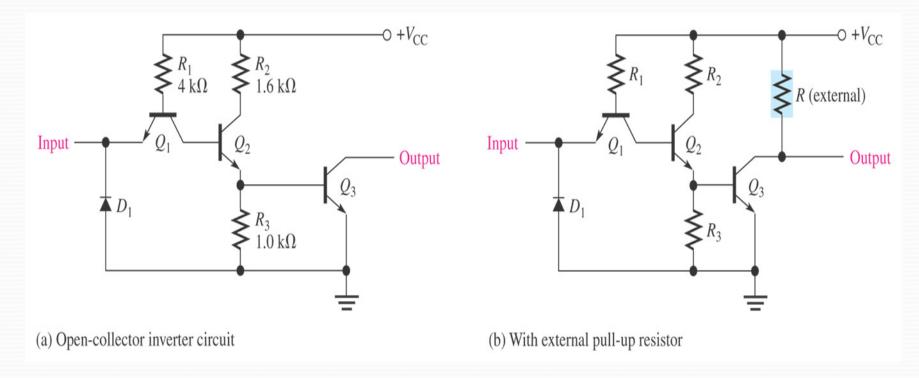


Diode equivalent of a TTL multiple-emitter transistor.

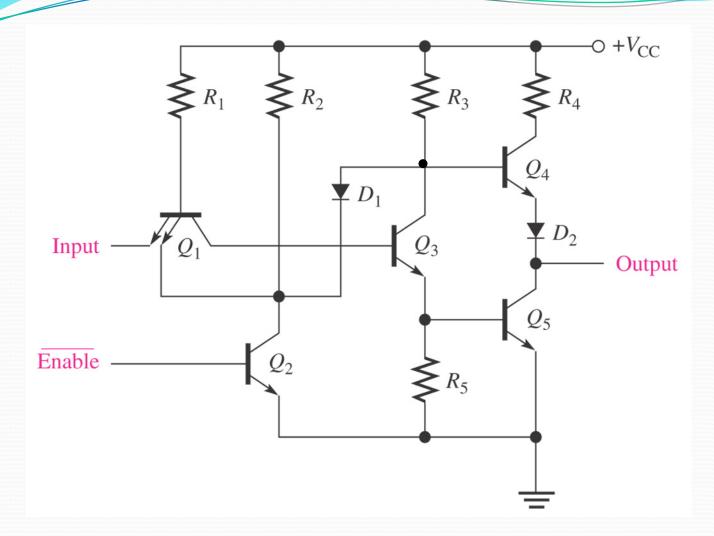


TTL inverter with open-collector output (Open-Collector Gates)

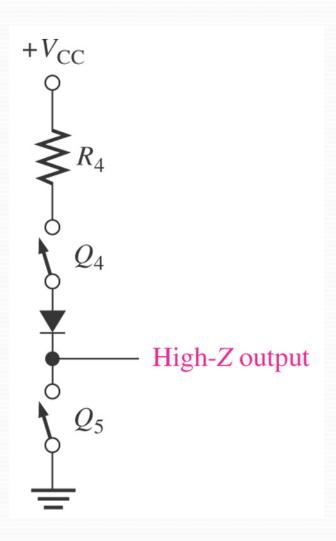




Basic tristate inverter circuit.

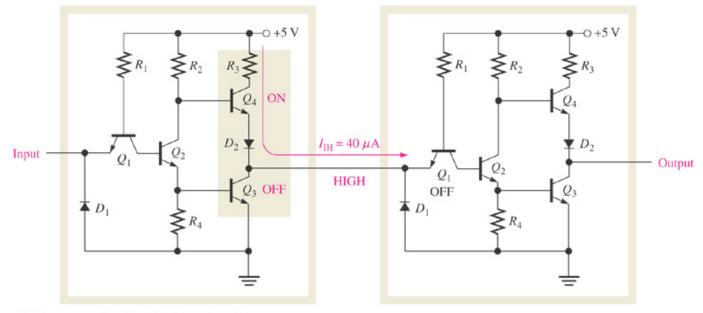


An equivalent circuit for the tristate output in the high-Z state

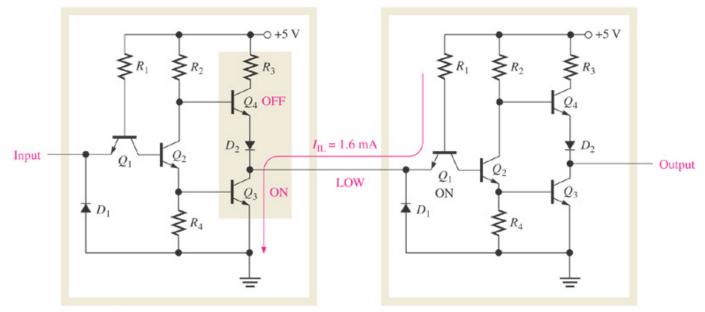


12.4 Practical Considerations in the Use of TTL

Current sinking and sourcing action in TTL.

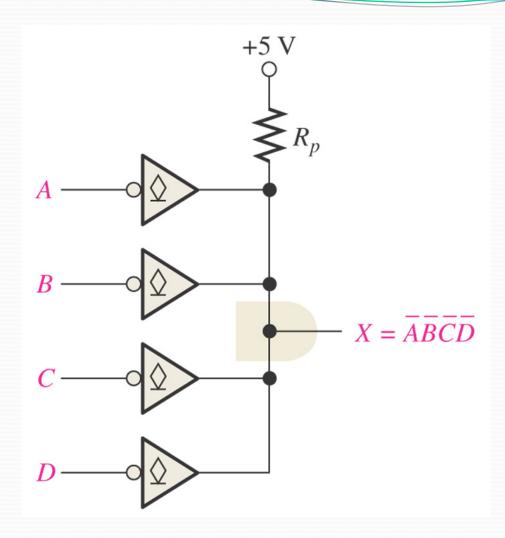


(a) Current sourcing (I_{IH} value is maximum)



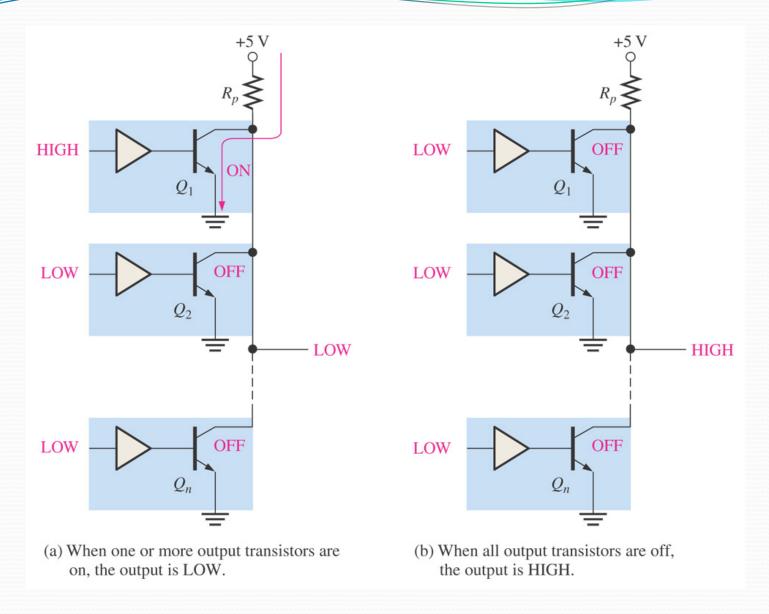
(b) Current sinking (I_{IL} value is maximum)

A wired-AND configuration of four inverters

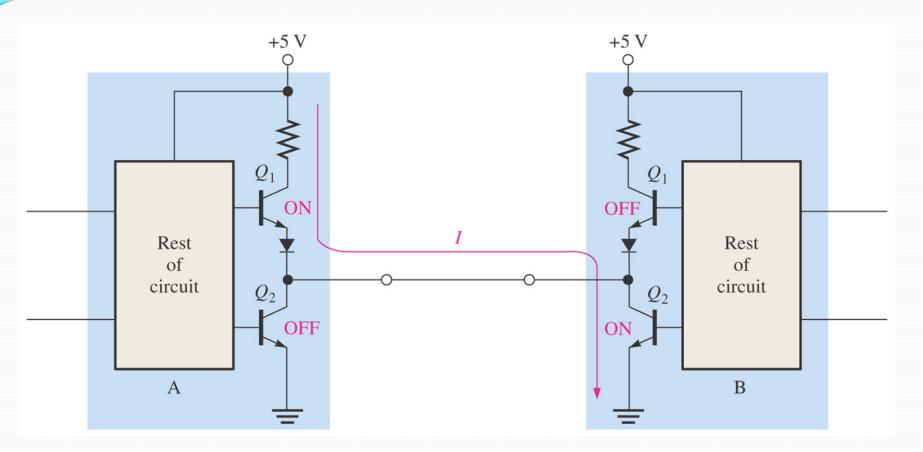


Wired-AND: The output of open-collector gates are wired together.

Open-collector wired negative-AND operation with inverters.



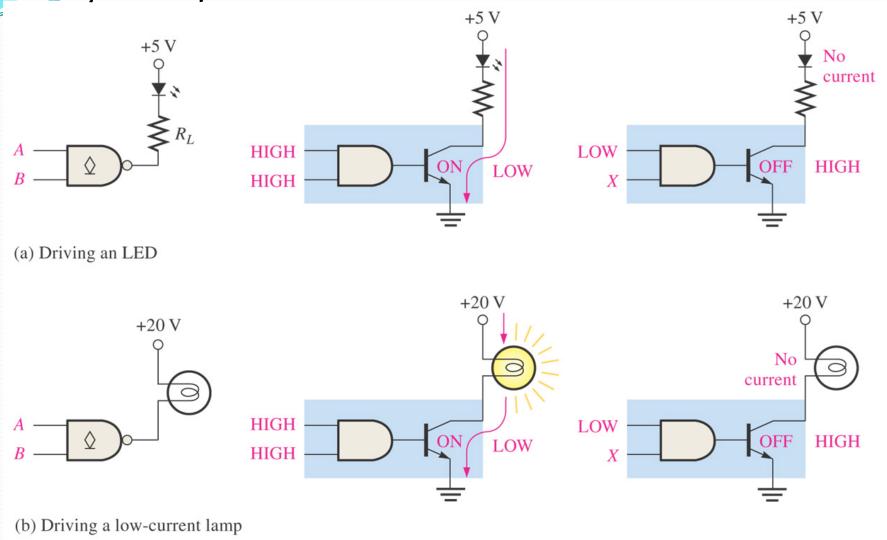
If the outputs of Totem-Pole are connected, ...?



Totem-pole outputs wired together. Such a connection may cause excessive current through Q_1 of device A and Q_2 of device B and should never be used.

45

Why an open-collector driver is so useful?

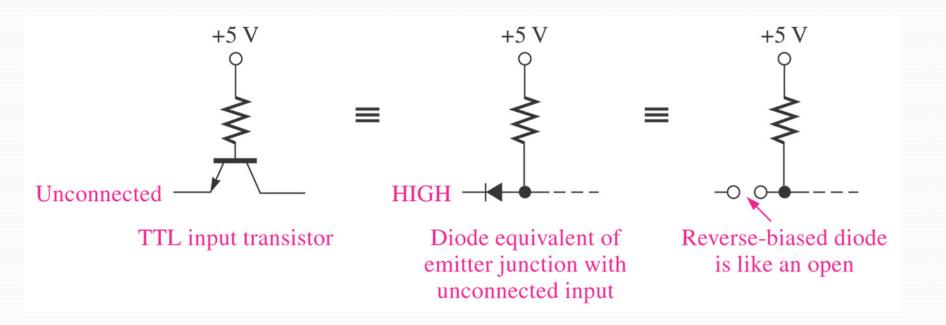


Some applications of open-collector drivers

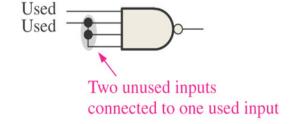
How do we set those unused TTL inputs?

- An unconnected input on a TTL gate acts as a HIGH
- An open input results in a reverse-biased emitter junction on the input transistor
- It is best **NOT** to leave unused TTL inputs unconnected.

Comparison of an open TTL input and a HIGH-level input.



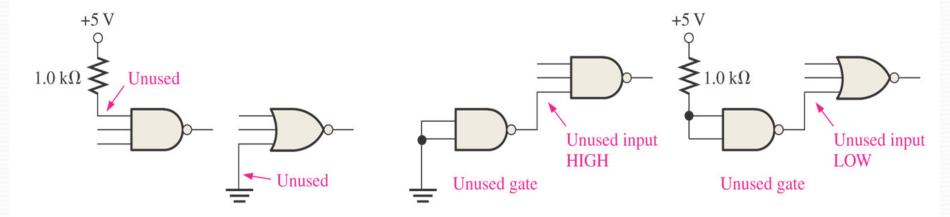
Methods for handling unused TTL inputs



This connection counts as: 1 unit load in LOW state 3 unit loads in HIGH state Two unused inputs connected to one used input

This connection counts as: 3 unit loads in LOW state 3 unit loads in HIGH state

(a) Tied-together inputs



(b) Inputs to V_{CC} or ground

(c) Inputs to unused output